

Abstract of the Disclosure

5 A method of forming a coupling dielectric in a memory cell includes forming an oxide on a substrate, forming Ta<sub>2</sub>O<sub>5</sub> on the oxide, oxidizing the Ta<sub>2</sub>O<sub>5</sub> with rapid thermal process (RTP) at a temperature above the crystallization temperature for Ta<sub>2</sub>O<sub>5</sub>, forming a cell nitride on the oxidized Ta<sub>2</sub>O<sub>5</sub>, and forming a wetgate oxide on the cell nitride.

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